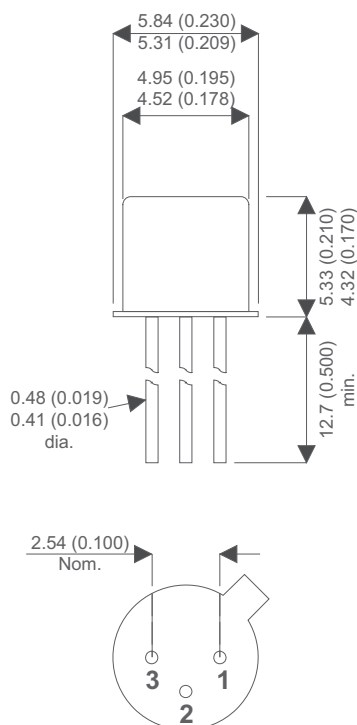


MECHANICAL DATA

Dimensions in mm (inches)



BIPOLAR NPN SILICON TRANSISTOR

FEATURES

- GENERAL PURPOSE NPN TRANSISTOR
- HERMETICALLY SEALED METAL PACKAGE
- JAN LEVEL SCREENING OPTIONS
- CECC LEVEL SCREENING OPTIONS

TO-18 (TO-206AA) METAL PACKAGE

Underside View

PIN 1 – Emitter PIN 2 – Base PAD 3 – Collector

ABSOLUTE MAXIMUM RATINGS ($T_{case} = 25^{\circ}C$ unless otherwise stated)

V_{CBO}	Collector – Base Voltage	200V
V_{CEO}	Collector – Emitter Voltage	140V
V_{EBO}	Emitter – Base Voltage	15V
I_C	Continuous Collector Current	30mA
P_{tot}	Power Dissipation	360mW
$R_{\theta JC}$	Thermal Resistance Junction to Case	417°C/W
T_J, T_{stg}	Operating and Storage Temperature	-55 to 175°C

Semelab Plc reserves the right to change test conditions, parameter limits and package dimensions without notice. Information furnished by Semelab is believed to be both accurate and reliable at the time of going to press. However Semelab assumes no responsibility for any errors or omissions discovered in its use. Semelab encourages customers to verify that datasheets are current before placing orders.

ELECTRICAL CHARACTERISTICS ($T_C = 25^\circ\text{C}$ unless otherwise stated)

Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$V_{(BR)CBO}$ Collector – Base Breakdown Voltage	$I_C = 100\mu\text{A}$ $I_E = 0$	200			V
$V_{(BR)CEO}$ Collector – Emitter Breakdown Voltage	$I_C = 10\text{mA}$ $I_B = 0$	140			
$V_{(BR)EBO}$ Emitter – Base Breakdown Voltage	$I_E = 100\mu\text{A}$ $I_C = 0$	15			
I_{CBO} Collector – Base Cut-off Current	$V_{CB} = 150\text{V}$ $I_E = 0$			1.0	μA
$V_{CE(sat)}$ Collector – Emitter Saturation Voltage	$I_C = 10\text{mA}$			1.0	V
h_{FE} Static Forward Current Transfer Ratio	$I_C = 10\text{mA}$ $V_{CE} = 10\text{V}$	40		200	---